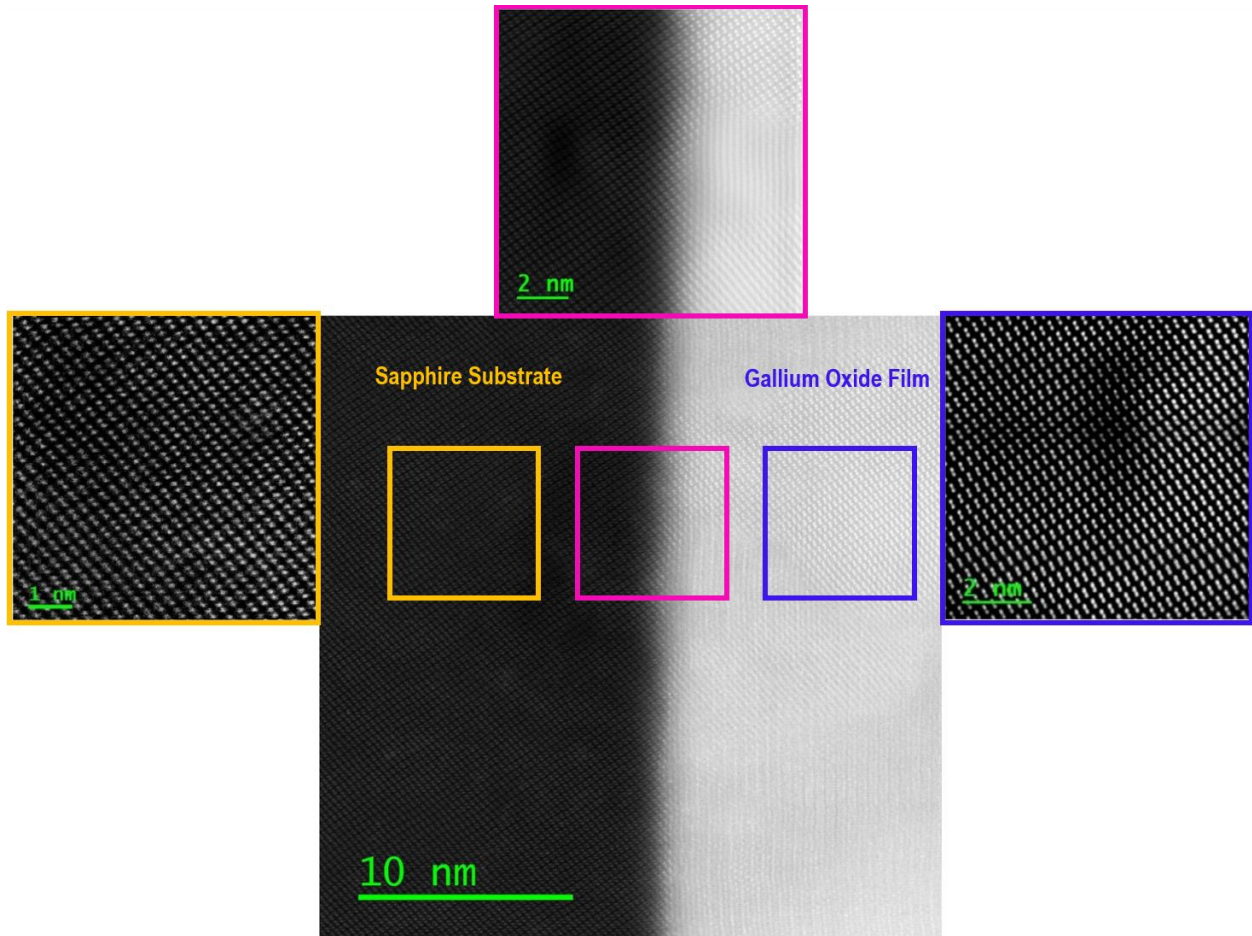


Abstract Title: ALD-grown gallium oxide thin films with properties close to bulk wafers

Attachment:



Cross section of a gallium oxide film deposited at 275°C by ALD on a C-plane sapphire substrate showing the film, the substrate and their interface. Images are obtained with High Angle Annular Dark Field (HAADF) STEM microscopy at 200 kV using a JEOL JEM-ARM200CF Atomic Resolution S/TEM instrument. Cross section TEM lamella was prepared on a ThermoFisher Helios G4 PFIB UXe DualBeam system.